

N-Channel 650V (D-S) Power MOSFET

PRODUCT SUMMARY

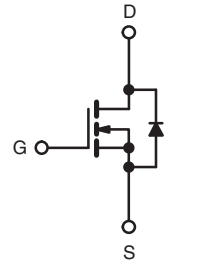
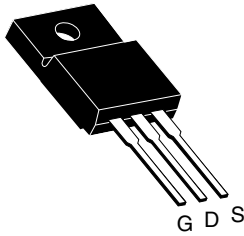
V_{DS} (V)	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10\text{ V}$	0.17
Q_g max. (nC)	109	
Q_{gs} (nC)	15	
Q_{gd} (nC)	31	
Configuration	Single	

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



TO-220 FULLPAK



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	650	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	20	A
		$T_C = 100\text{ }^{\circ}\text{C}$		13	
Pulsed Drain Current ^a			I_{DM}	56	
Linear Derating Factor				1.8	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ^b			E_{AS}	691	mJ
Maximum Power Dissipation			P_D	30	W
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Drain-Source Voltage Slope	$T_J = 125\text{ }^{\circ}\text{C}$		dV/dt	70	V/ns
Reverse Diode dV/dt ^d		26			
Soldering Recommendations (Peak Temperature) ^c	for 10 s			300	$^{\circ}\text{C}$

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 28.2\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 7\text{ A}$.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100\text{ A}/\mu\text{s}$, starting $T_J = 25\text{ }^{\circ}\text{C}$.

THERMAL RESISTANCE RATINGS

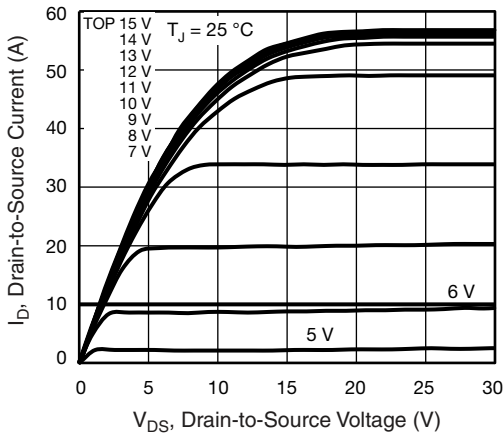
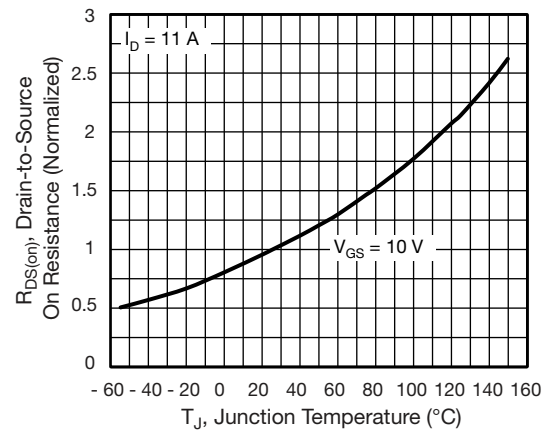
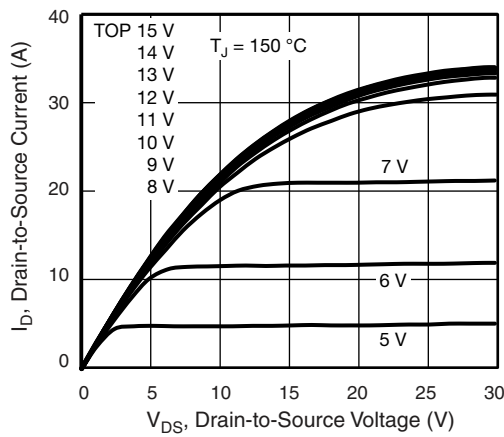
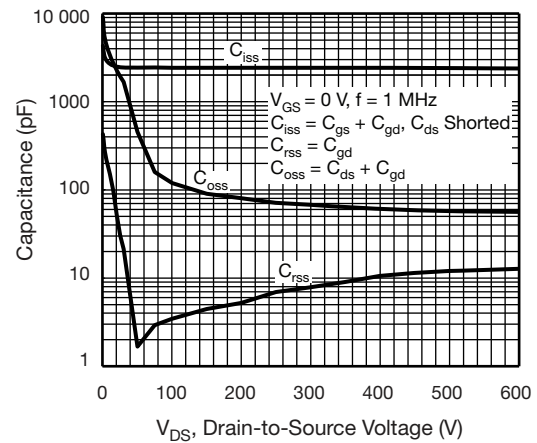
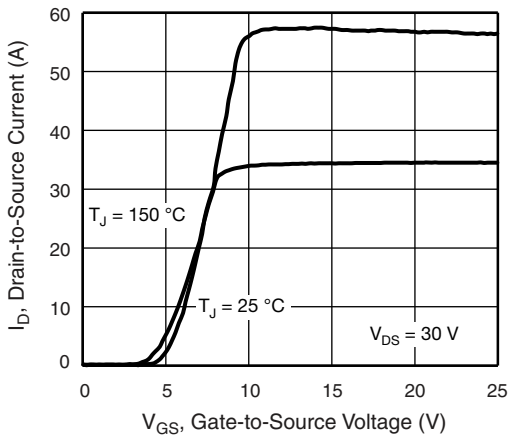
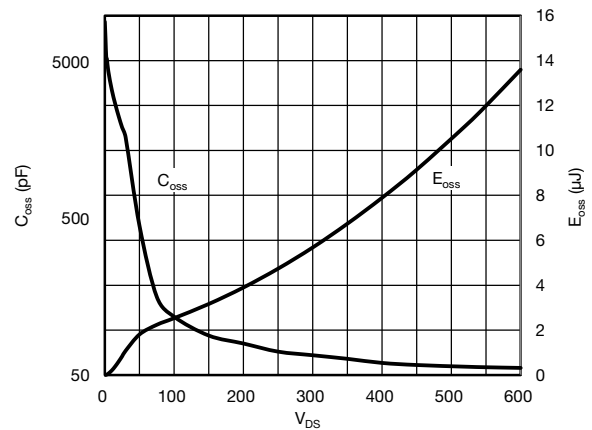
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.6	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		650	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.74	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		3	-	5	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
		V _{GS} = ± 30 V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 520 V, V _{GS} = 0 V, T _J = 125 °C		-	-	10	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 11 A	-	0.170	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = 8 V, I _D = 5 A		-	6.7	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	2414	-	pF
Output Capacitance	C _{oss}			-	118	-	
Reverse Transfer Capacitance	C _{rss}			-	4	-	
Effective Output Capacitance, Energy Related ^a	C _{o(er)}	V _{DS} = 0 V to 520 V, V _{GS} = 0 V		-	89	-	
Effective Output Capacitance, Time Related ^b	C _{o(tr)}			-	307	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 11 A, V _{DS} = 520 V	-	73	110	nC
Gate-Source Charge	Q _{gs}			-	15	-	
Gate-Drain Charge	Q _{gd}			-	32	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 520 V, I _D = 11 A, V _{GS} = 10 V, R _g = 9.1 Ω		-	22	45	ns
Rise Time	t _r			-	33	66	
Turn-Off Delay Time	t _{d(off)}			-	73	110	
Fall Time	t _f			-	38	76	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	0.64	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	22	A
Pulsed Diode Forward Current	I _{SM}			-	-	56	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 11 A, V _{GS} = 0 V		-	-	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 11 A, dI/dt = 100 A/μs, V _R = 400 V		-	400	-	ns
Reverse Recovery Charge	Q _{rr}			-	5.9	-	μC
Reverse Recovery Current	I _{RRM}			-	20	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

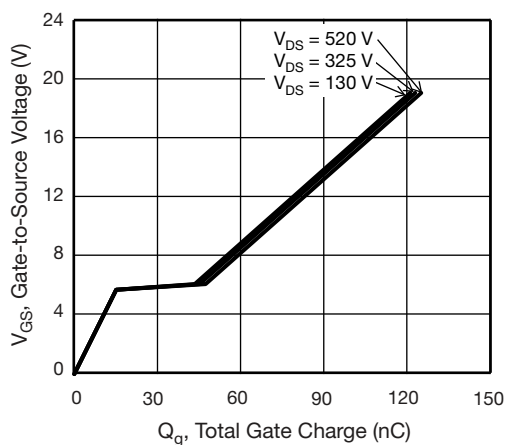


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

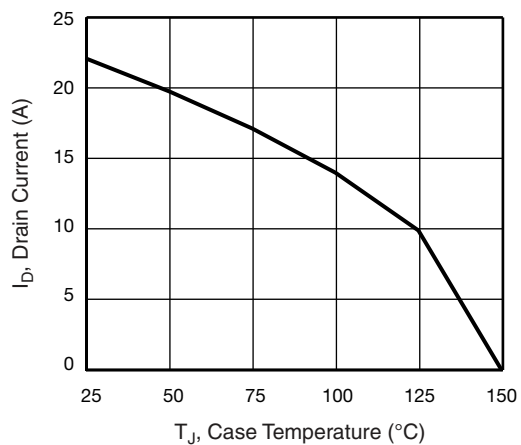


Fig. 10 - Maximum Drain Current vs. Case Temperature

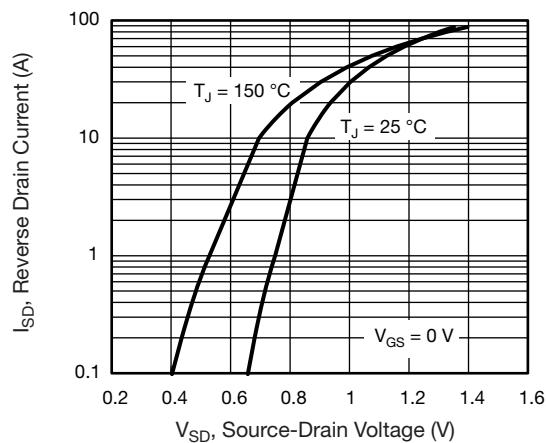


Fig. 8 - Typical Source-Drain Diode Forward Voltage

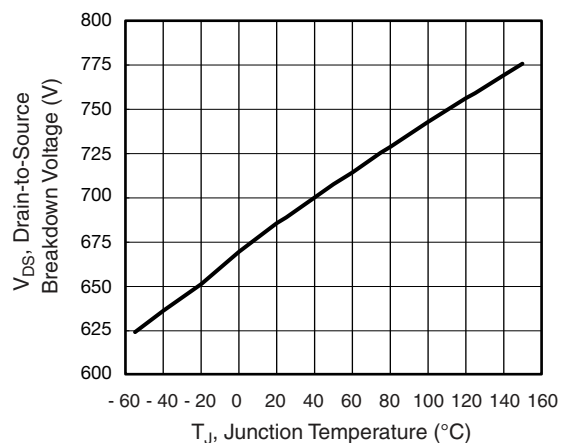


Fig. 11 - Temperature vs. Drain-to-Source Voltage

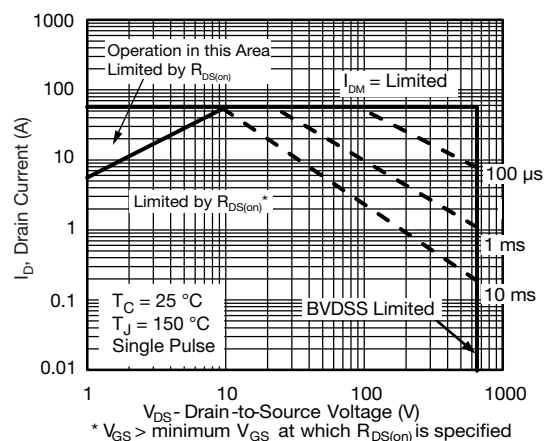


Fig. 9 - Maximum Safe Operating Area

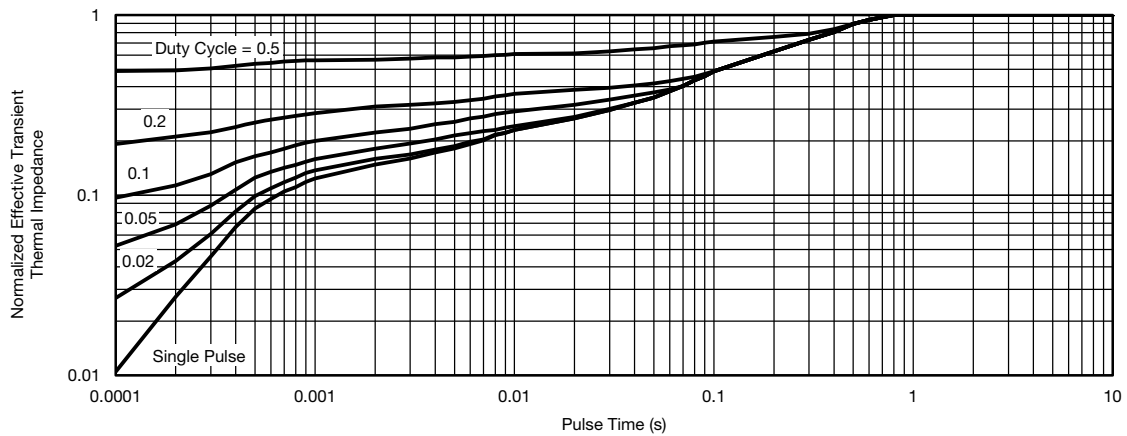


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

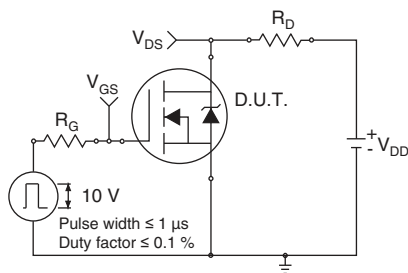


Fig. 13 - Switching Time Test Circuit

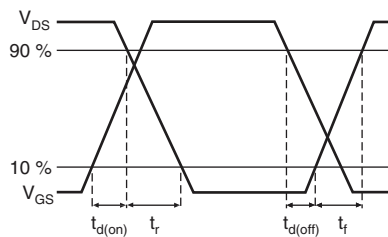


Fig. 14 - Switching Time Waveforms

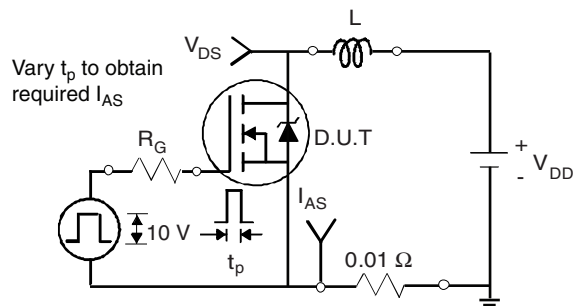


Fig. 15 - Unclamped Inductive Test Circuit

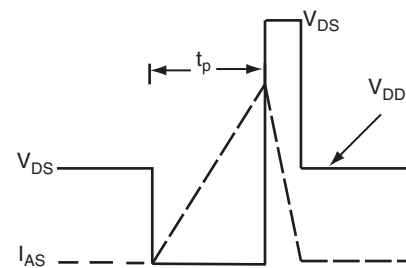


Fig. 16 - Unclamped Inductive Waveforms

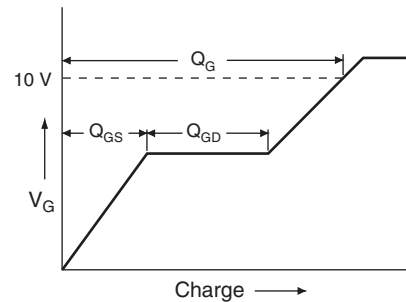


Fig. 17 - Basic Gate Charge Waveform

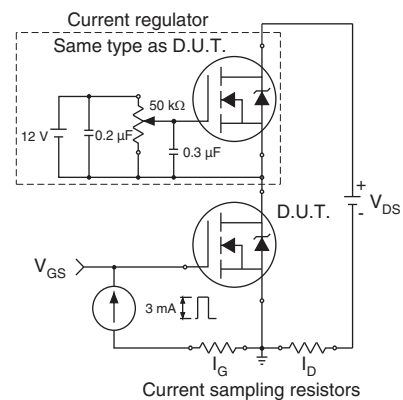
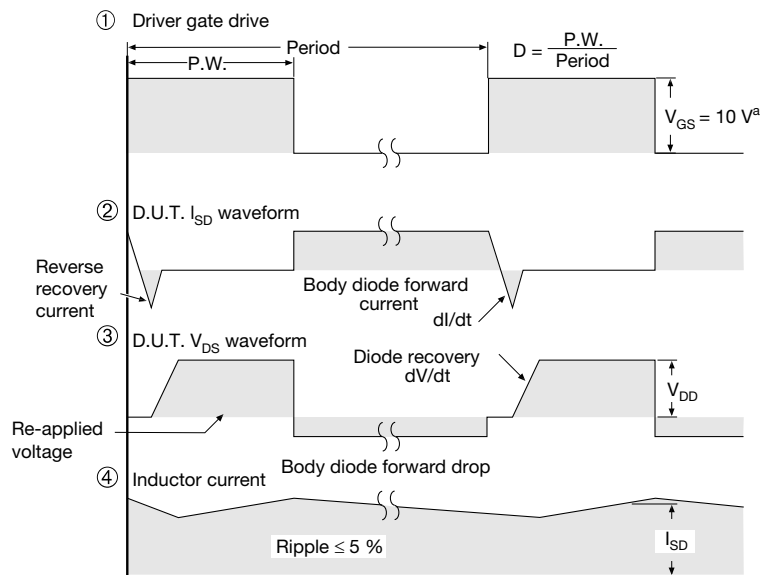
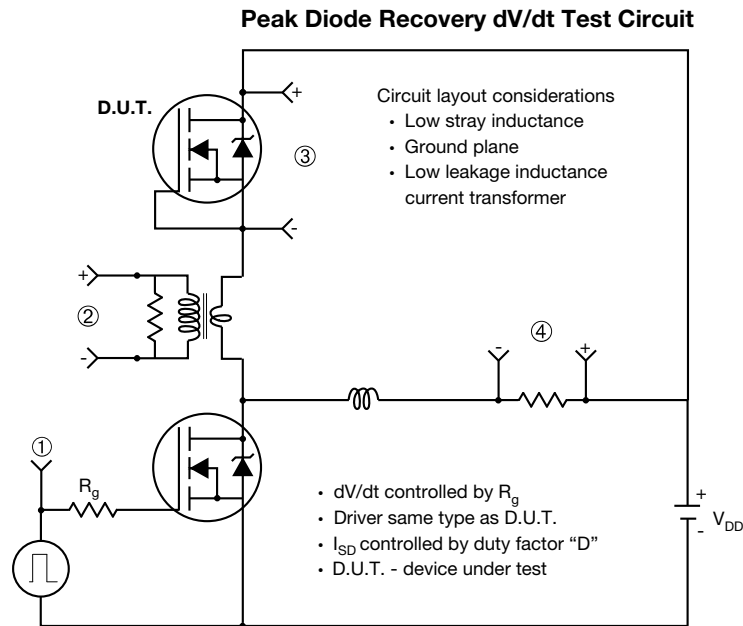
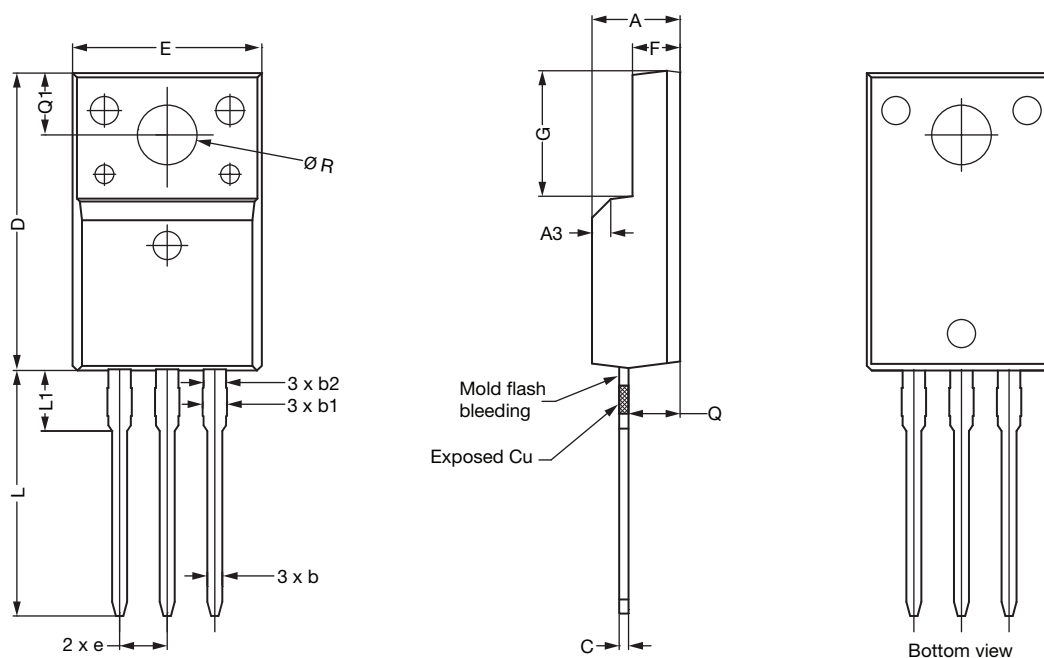


Fig. 18 - Gate Charge Test Circuit

**Note**a. $V_{GS} = 5 V$ for logic level devices**Fig. 19 - For N-Channel**

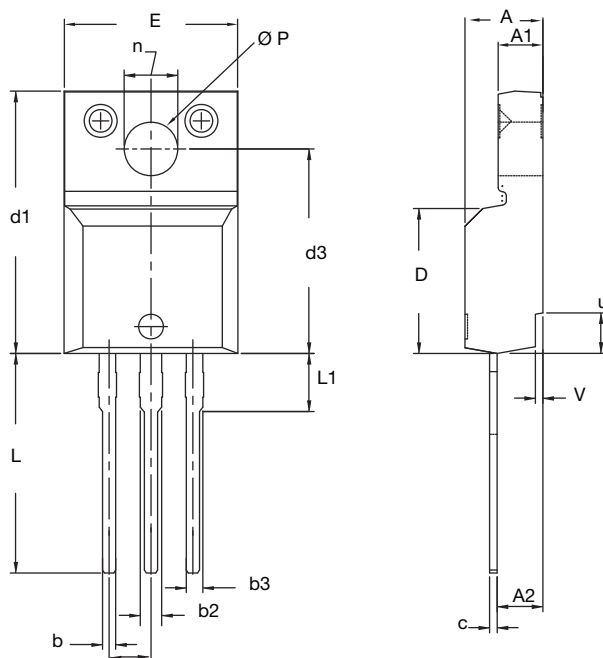
TO-220 FULLPAK



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54 BSC		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
$\varnothing R$	3.08	3.18	3.28

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

FACILITY

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

ECN: E19-0180-Rev. D, 08-Apr-2019
DWG: 5972

Notes

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2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

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